Docket No.: 12054-0023

## DECLARATION AND POWER OF ATTORNEY

As a below named inventor, I declare that:

My residence, post office address, and citizenship are as stated below next to my name. I believe that I am the original, first and sole inventor (if only one name is listed below) or an original, first, and joint inventor (if plural names are listed below) of the subject matter that is claimed and for which a patent is sought on the invention entitled

## HEAT TREATMENT JIG FOR SEMICONDUCTOR SUBSTRATE AND METHOD OF HEAT TREATING SEMICONDUCTOR SUBSTRATE

the specification of which is attached was filed on		application Serial No.	$_{f L}$ , and (if applicable) was
I hereby state that I have reviewed and understand	d the contents of the above identified spe	ecification, including the claims, as amended by any	y amendment referred to above.
I acknowledge the duty to disclose information of	vhich I am aware and which is material t	o the examination of the patent application in accor	rdance with 37 CFR §1.56.
	other than the United States, listed below	eign application(s) for patent or inventor's certificat w and have also identified below, by checking the s he application on which priority is not claimed.	
Prior Foreign Application(s)			
Number	Country	Day/Month/Year Filed	<b>Priority Not Claimed</b>
2003-378724	Japan	07/NOV/2003	
I hereby claim the benefit under 35 U.S.C. §119(e	of any United States provisional applica	ation(s) listed below	
	Serial Number	Filing Date	
insofar as the subject matter of each of the claims	s of this application is not disclosed in the duty to disclose information known to me	65(c) of any PCT International application designate prior United States or PCT International application which is material to the patentability as defined in ate of this application. Status (patented, pending, aba	tion in the manner provided by the first 37 CFR §1.56 which became available
attorneys with full power of substitution to prose Send Correspondence to: CLARK & BRODY, I hereby declare that all statements made herein of	ecute the subject application and to tra 1750 K Street, NW, Suite 600, Wash of my own knowledge are true and that a ful false statements and the like so made	No. 30,340) and CHRISTOPHER W. BRODY insact all business in the Patent and Trademark nington, DC 20006; Telephone: 202-835-111 all statement made on information and belief are be are punishable by fine or imprisonment, or both, und	Office connected therewith.  1; Facsimile: 202-835-1755.  lieved to be true; and further that these
		or any patent issued thereon.	
Full name of sole or first inventor: Naoshi A	DACHI	or any patent issued thereon.	
		or any patent issued thereon.  Date:	
Inventor's signature:			
Inventor's signature:		Date:	
Inventor's signature:Residence:Citizenship:		Date:	
Inventor's signature:	omo Mitsubishi Silicon Corporation, 1	Date:	an
Inventor's signature:	omo Mitsubishi Silicon Corporation, 1. azushi YOSHIDA	Date: -2-1, Shibaura, Minato-ku, Tokyo 105-8634 Japa	30
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Inventor's signature:	omo Mitsubishi Silicon Corporation, 1. azushi YOSHIDA	Date:	30
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Inventor's signature:	Date:
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Inventor's signature:	Date:
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Citizenship:	
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Full name of fifth joint inventor, if any:	
Inventor's signature:	Date:
Residence:	
Citizenship:	
Post Office Address:	
Tost Office Address.	
Full name of sixth joint inventor, if any:	
Inventor's signature:	
Residence:	
Citizenship: Post Office Address:	
POST UTILICE ADDITESS:	